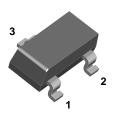
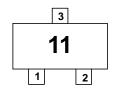


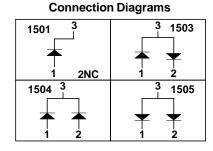
# MMBD1501/A / 1503/A / 1504/A / 1505/A



**SOT-23** 



MARKING MMBD1501 11 MMBD1501A A11 MMBD1503 13 MMBD1503A A13 MMBD1504 14 MMBD1504A A14 MMBD1505 15 MMBD1505A A15



# **Small Signal Diodes**

**Absolute Maximum Ratings\*** T<sub>4</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{RRM}$	Maximum Repetitive Reverse Voltage	200	V
I <sub>F(AV)</sub>	Average Rectified Forward Current	200	mA
I <sub>FSM</sub>	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	1.0 2.0	A A
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
TJ	Operating Junction Temperature	150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### **Thermal Characteristics**

Symbol	Parameter	Value	Units
$P_{D}$	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

### **Electrical Characteristics** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
V <sub>R</sub>	Breakdown Voltage	$I_R = 5.0  \mu A$	200		V
V <sub>F</sub>	Forward Voltage	$\begin{array}{l} I_F = 1.0 \text{ mA} \\ I_F = 10 \text{ mA} \\ I_F = 50 \text{ mA} \\ I_F = 100 \text{ mA} \\ I_F = 200 \text{ mA} \\ I_F = 300 \text{ mA} \end{array}$	620 720 800 830 0.87 0.90	720 830 890 930 1.1 1.15	mV mV mV V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 125 V V <sub>R</sub> = 125 V, T <sub>A</sub> = 150°C V <sub>R</sub> = 180 V V <sub>R</sub> = 180 V, T <sub>A</sub> = 150°C		1.0 3.0 10 5.0	nA μA nA μA
C <sub>T</sub>	Total Capacitance	$V_R = 0$ , $f = 1.0 \text{ MHz}$		4.0	PF

<sup>1)</sup> These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

### **Small Signal Diode**

(continued)

### **Typical Characteristics**

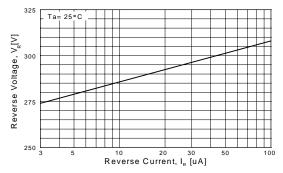


Figure 1. Reverse Voltage vs Reverse Current BV - 3.0 to 100 uA

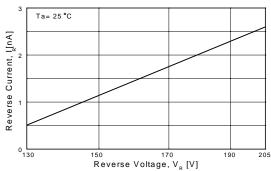


Figure 2. Reverse Current vs Reverse Voltage IR - 130 - 250 Volts

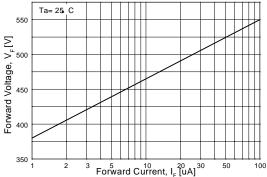


Figure 3. Forward Voltage vs Forward Current VF - 1 to 100 uA

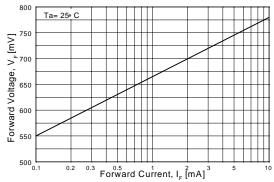


Figure 4. Forward Voltage vs Forward Current VF - 0.1 to 10 mA

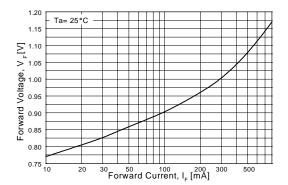


Figure 5. Forward Voltage vs Forward Current VF - 10 to 800 mA

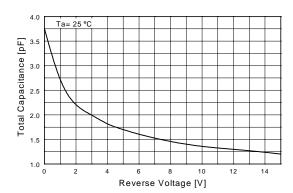


Figure 6. Total Capacitance vs Reverse Voltage VR - 0 to 15 V

# **Small Signal Diode**

(continued)

## Typical Characteristics (continued)

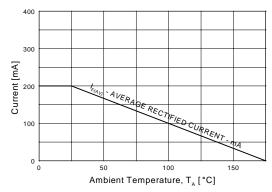


Figure 7. Average Rectified Current ( $I_{F(AV)}$ ) versus Ambient Temperature ( $T_A$ )

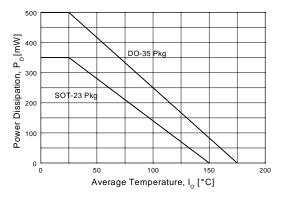


Figure 8. Power Derating Curve

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E	coSPARK™	GTO™ .	MSX™	QT Optoelectronics™	TinyLogic <sup>®</sup>
$E^2$	<sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
Er	nSigna™	I <sup>2</sup> C <sup>TM</sup>	$OCX^{TM}$	RapidConfigure™	UHC™
A	cross the board.	Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
Th	ne Power Franch	nise™	OPTOLOGIC®	SILENT SWITCHER®	VCX™
Pı	rogrammable Ac	tive Droop™	OPTOPLANAR™	SMART START™	

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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